NPN Silicon Transistors

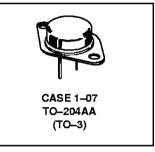
... fast switching speeds and high current capacity ideally suit these parts for use in switching regulators, inverters, wide-band amplifiers and power oscillators in industrial and commercial applications.

- High Speed t_f = 0.5 μs (Max)
- High Current I_{C(max)} = 30 Amps
 Low Saturation V_{CE(sat)} = 2.5 V (Max) @ I_C = 20 Amps

2N5038* 2N5039

*Motorola Preferred Device

20 AMPERE **NPN SILICON POWER TRANSISTORS** 75 and 90 VOLTS **140 WATTS**



*MAXIMUM RATINGS

Rating	Symbol	2N5038	2N5039	Unit
Collector-Base Voltage	V _{CBO}	150	120	Vdc
Collector-Emitter Voltage	VCEV	150	120	Vdc
Emitter-Base Voltage	V _{EBO}	7		Vdc
Collector Current — Continuous Peak (1)	IC ICM	20 30		Adc
Base Current — Continuous	lΒ	5		Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	140 0.8		Watts W/°C
Operating and Storage Junction Temperature Range	TJ, T _{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R ₀ JC	1.25	°C/W

^{*} Indicates JEDEC Registered Data.

⁽¹⁾ Pulse Test: Pulse Width ≤ 10 ms, Duty Cycle ≤ 50%.

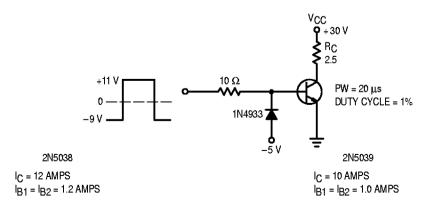


Figure 1. Switching Time Test Circuit

Preferred devices are Motorola recommended choices for future use and best overall value. REV 7



*ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

	Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERIS	TICS					•
Collector–Emitter Su (I _C = 200 mAdc, I	3 7	2N5038 2N5039	V _{CEO(sus)}	90 75	_	Vdc
	VBE(off) = 1.5 V)	2N5038 2N5039 2N5038 2N5039	^I CEX	_ _ _ _	50 50 10 10	mAdc
Emitter Cutoff Curre (V _{EB} = 5 Vdc, I _C : (V _{EB} = 7 Vdc, I _C :	= 0)	2N5038 2N5039 Both	I _{EBO}	_ _ _	5 15 50	mAdc
ON CHARACTERIST	ICS (1)					
DC Current Gain (I _C = 12 Adc, V _{CE} (I _C = 10 Adc, V _{CE}		2N5038 2N5039	hFE	20 20	100 100	_
Collector-Emitter Sa (IC = 20 Adc, IB =	-		V _{CE(sat)}	_	2.5	Vdc
Base-Emitter Satura (I _C = 20 Adc, I _B =	•		V _{BE(sat)}	_	3.3	Vdc
DYNAMIC CHARACT	TERISTICS					•
Forward Current 1	on–Emitter Small–Signal Short–Circuit ransfer Ratio = 10 Vdc, f = 5 MHz)		h _{fe}	12	_	_
SWITCHING CHARA	CTERISTICS					-
RESISTIVE LOAD						
Rise Time	(V _{CC} = 30 Vdc)		t _r	_	0.5	με
Storage Time	(I _C = 12 Adc, I _{B1} = I _{B2} = 1.2 Adc)	2N5038	t _s	_	1.5	με
Fall Time	(IC = 10 Adc, IB1 = IB2 = 1 Adc)	2N5039	tf	_	0.5	με

^{*} Indicates JEDEC Registered Data.

⁽¹⁾ Pulse Test: Pulse Width ≤ 300, µs, Duty Cycle ≤ 2%.

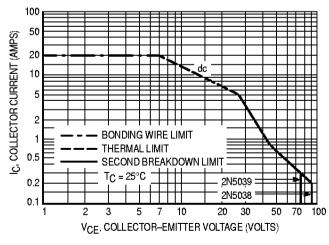
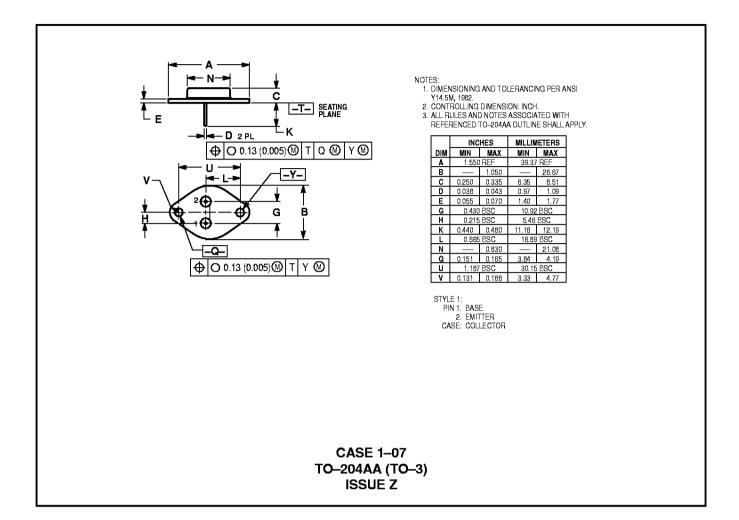


Figure 2. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC – VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

Second breakdown pulse limits are valid for duty cycles to 10%. At high case temperatures, thermal limitations may reduce the power that can be handled to values less than the limitations imposed by second breakdown.

PACKAGE DIMENSIONS



2N5038 2N5039

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